

**Description**

The LMP0160F uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

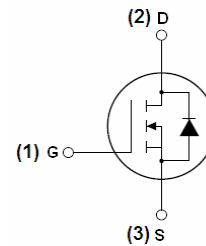
- $V_{DS} = 100V, I_D = 60A$
 $R_{DS(ON)} = 9.2m\Omega$ (typical) @ $V_{GS} = 10V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

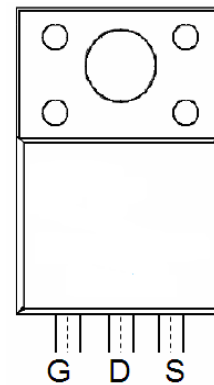
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔV_{ds} TESTED!



Schematic diagram



TO-220F top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP0160F	LMP0160F	TO-220F	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	60	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	42.4	A
Pulsed Drain Current	I_{DM}	240	A
Maximum Power Dissipation	P_D	40	W
Derating factor		0.27	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	290	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

**Thermal Characteristic**

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	3.75	$^{\circ}C/W$
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Electrical Characteristics ($T_C=25^{\circ}C$ unless otherwise noted)

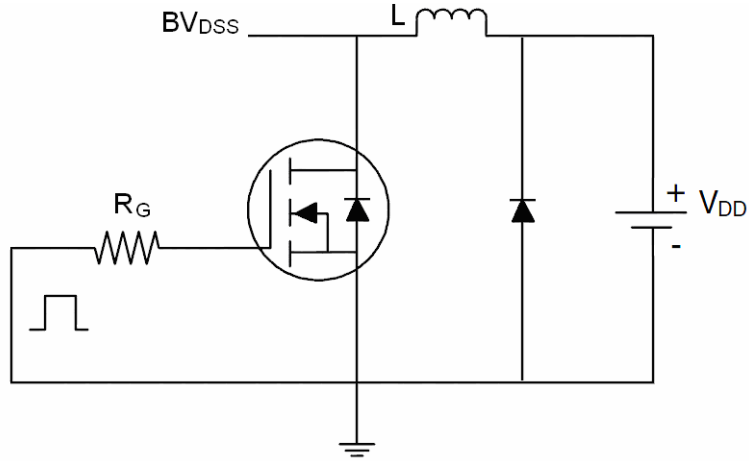
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=30A$	-	9.2	10.8	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=30A$	-	45	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{ISS}	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0MHz$	-	2500	-	PF
Output Capacitance	C_{OSS}		-	273	-	PF
Reverse Transfer Capacitance	C_{RSS}		-	27	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=50V, I_D=30A$ $V_{GS}=10V, R_G=4.7\Omega$	-	13	-	nS
Turn-on Rise Time	t_r		-	8.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	29	-	nS
Turn-Off Fall Time	t_f		-	4	-	nS
Total Gate Charge	Q_g	$V_{DS}=50V, I_D=30A,$ $V_{GS}=10V$	-	37		nC
Gate-Source Charge	Q_{gs}		-	14		nC
Gate-Drain Charge	Q_{gd}		-	8		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=60A$	-		1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	60	A
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}C, I_F = I_S$ $di/dt = 100A/\mu s$ ^(Note 3)	-	78		nS
Reverse Recovery Charge	Q_{rr}		-	149		nC

Notes:

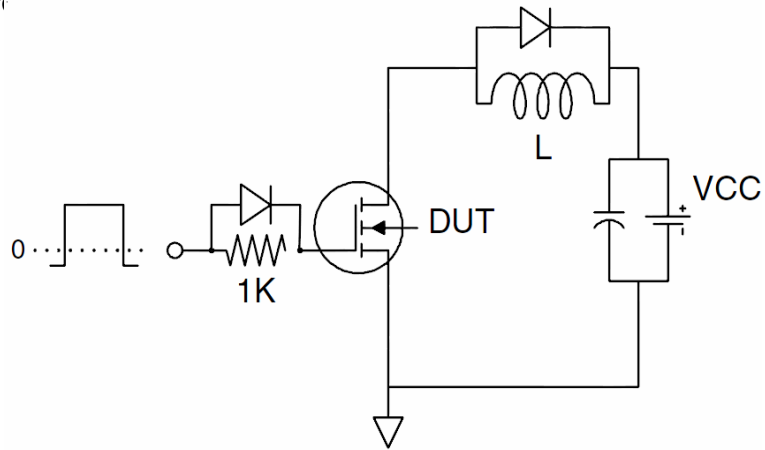
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^{\circ}C, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega$

Test Circuit

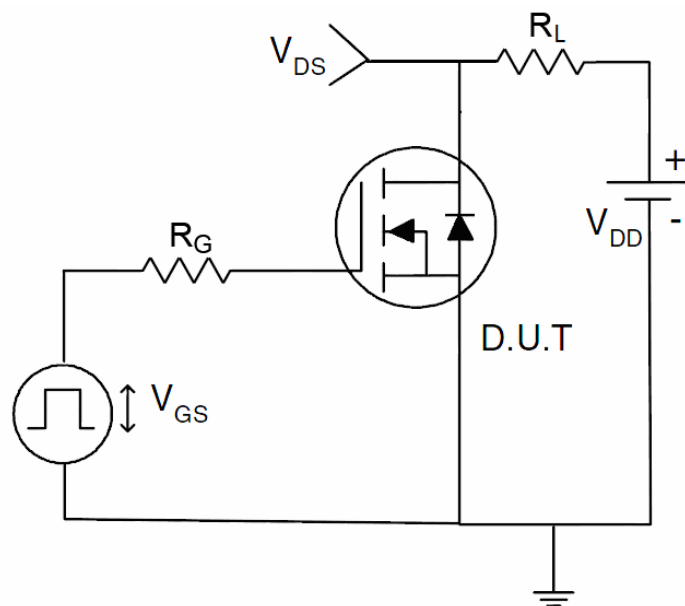
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

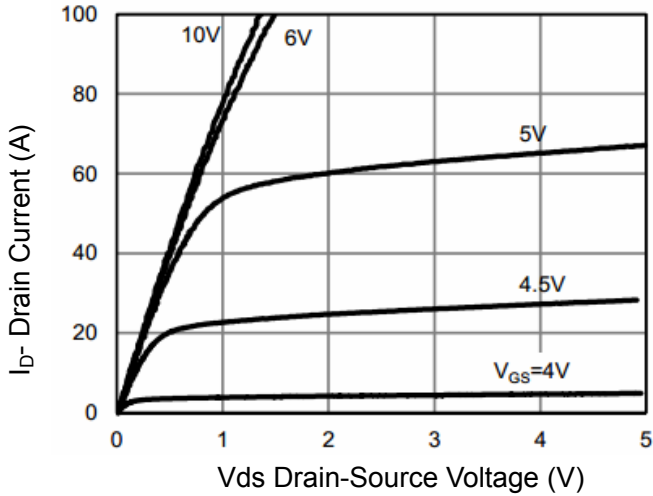


Figure 1 Output Characteristics

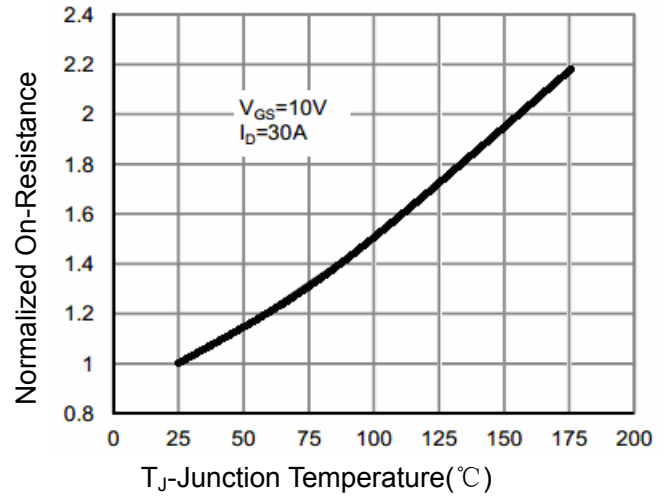


Figure 4 Rds(on)-Junction Temperature

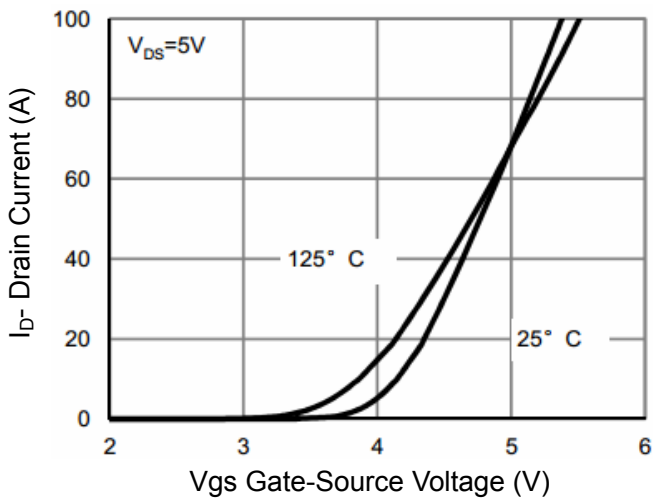


Figure 2 Transfer Characteristics

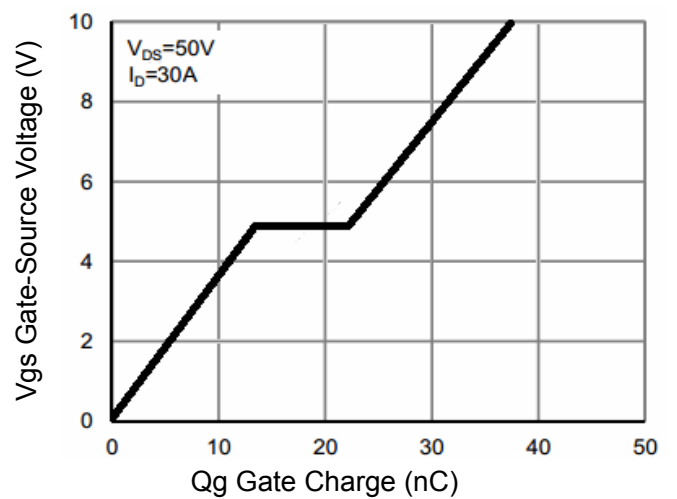


Figure 5 Gate Charge

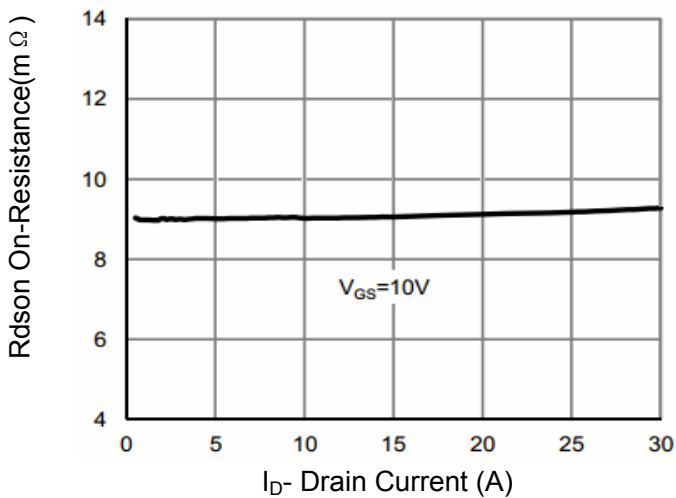


Figure 3 Rdson- Drain Current

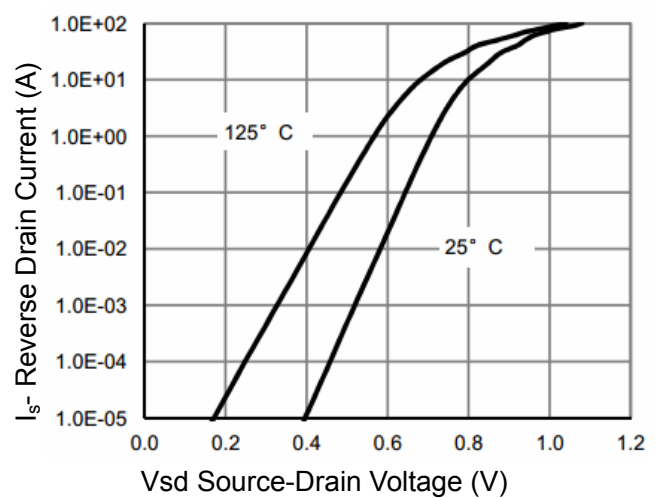


Figure 6 Source- Drain Diode Forward

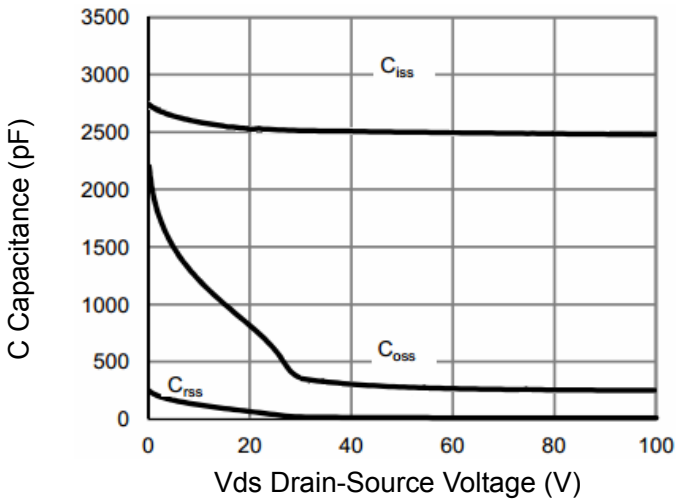


Figure 7 Capacitance vs Vds

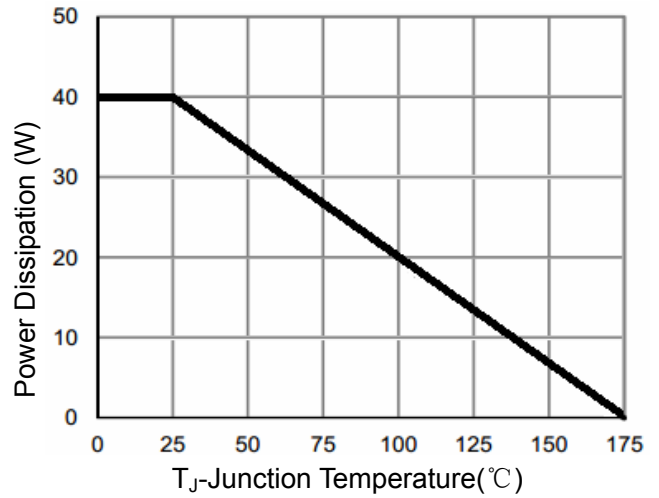


Figure 9 Power De-rating

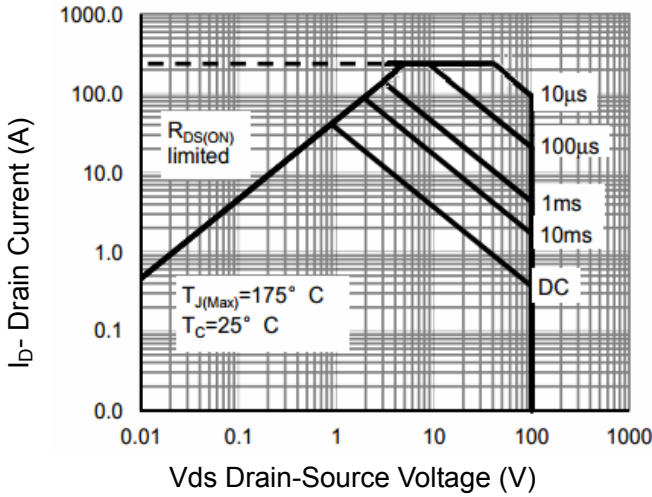


Figure 8 Safe Operation Area

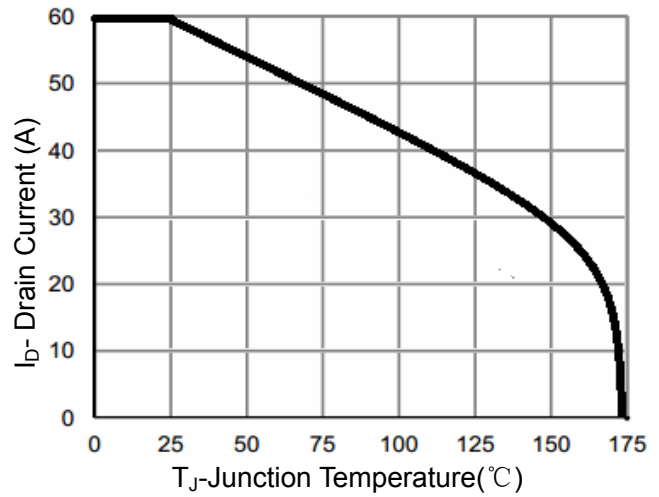


Figure 10 Current De-rating

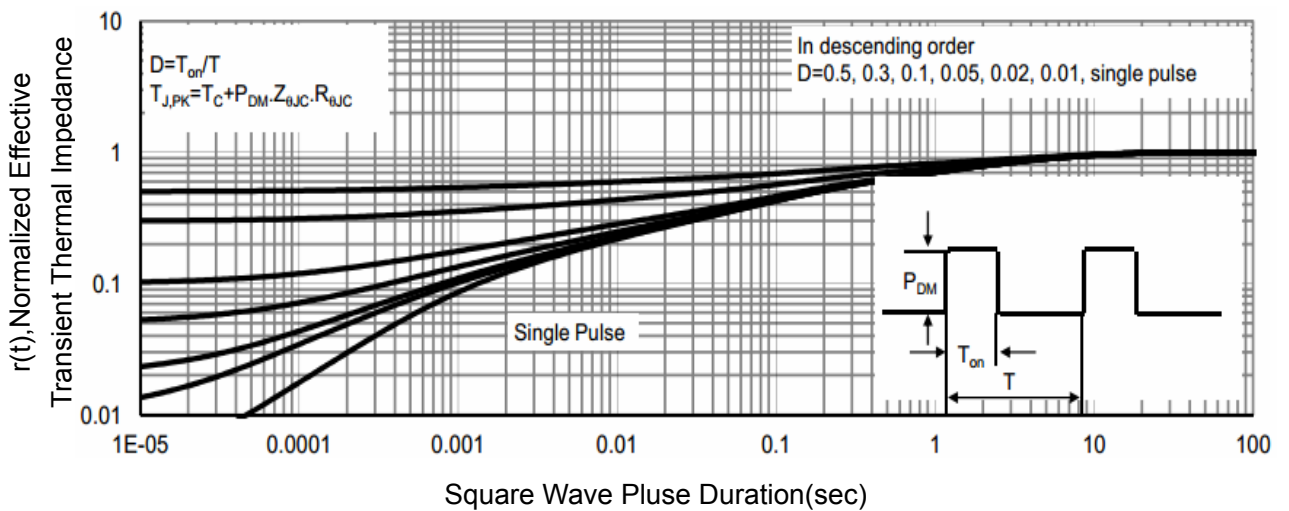
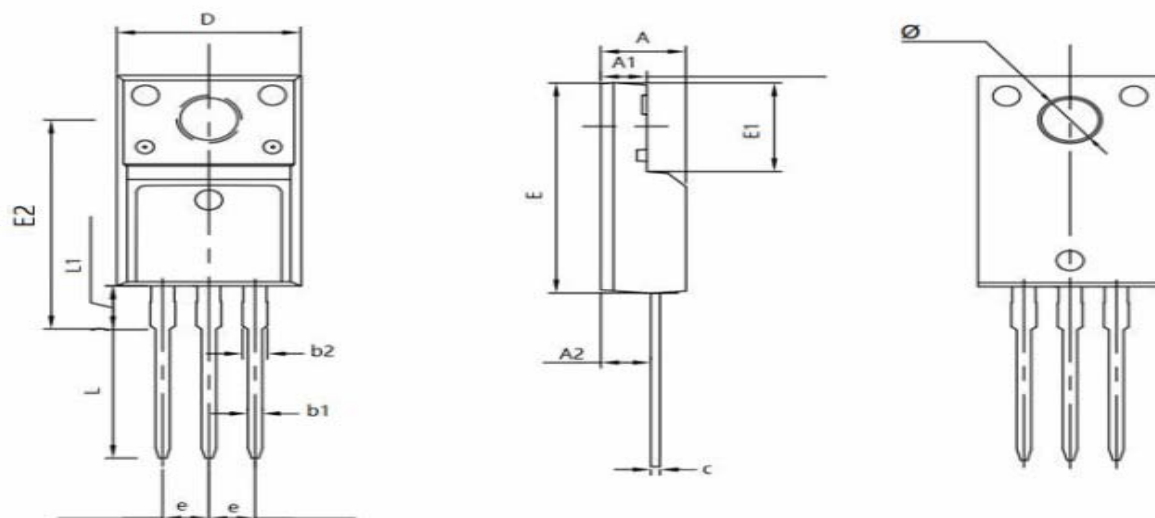


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-220F Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.500	4.900	0.177	0.193
A1	2.340	2.740	0.092	0.108
A2	2.560	2.960	0.101	0.117
b1	0.700	0.900	0.028	0.035
b2	1.180	1.580	0.046	0.062
c	0.400	0.600	0.016	0.024
D	9.960	10.360	0.392	0.408
E	15.670	15.970	0.617	0.629
E1	6.500	6.900	0.256	0.272
E2	15.500	16.100	0.610	0.634
e	2.540 TYP		0.100 TYP	
Φ	3.080	3.280	0.121	0.129
L	12.640	13.240	0.498	0.521
L1	3.030	3.430	0.119	0.135

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